

55V, 2A PNP/PNP low VCEsat (BISS) double transistor

11 December 2015

Product data sheet

1. General description

 $\label{eq:PNPPNP} \begin{array}{l} \text{In Small Signal (BISS) double transistor in a leadless} \\ \text{medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic} \\ \text{package with visible and solderable side pads.} \end{array}$

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor		·					
V _{CEO}	collector-emitter voltage	open base		-	-	-55	V
I _C	collector current			-	-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	А
Per transistor							
V _{CEsat}	collector-emitter saturation voltage	$\begin{split} & I_{C} = -0.7 \text{ A}; \ I_{B} = -7 \text{ mA}; \text{ pulsed}; \\ & t_{p} \leq 300 \mu s; \ \delta \leq 0.02 \ \ ; \ T_{amb} = 25 \ ^{\circ}\mathrm{C} \end{split}$		-	-300	-420	mV

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020D-6 (SOT1118D)	sym138
7	C1	collector TR1	DI 112020D-0 (3011110D)	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS5255PAPS	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D		

7. Marking

Table	e 4. Marking codes	
Туре	e number	Marking code
PBS	SS255PAPS	3N

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{CBO}	collector-base voltage	open emitter		-	-55	V
V _{CEO}	collector-emitter voltage	open base		-	-55	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	А
I _B	base current			-	-0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

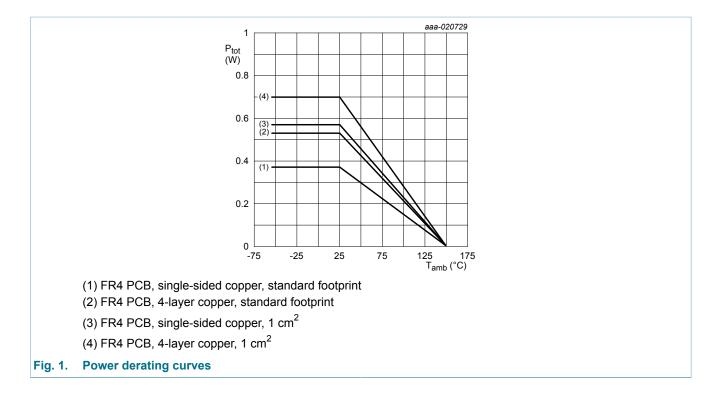
[3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

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9. Thermal characteristics

Cumb al	Parameter	Conditiona		Min	True		11.14
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
ang a)	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to		[2]	-	-	219	K/W
	ampient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
Per device							
R _{th(j-a)}	thermal resistance	ce in free air [1]	[1]	-	-	246	K/W
	from junction to ambient		[2]	-	-	161	K/W
	ampient		[3]	-	-	172	K/W
			[4]	-	-	131	K/W

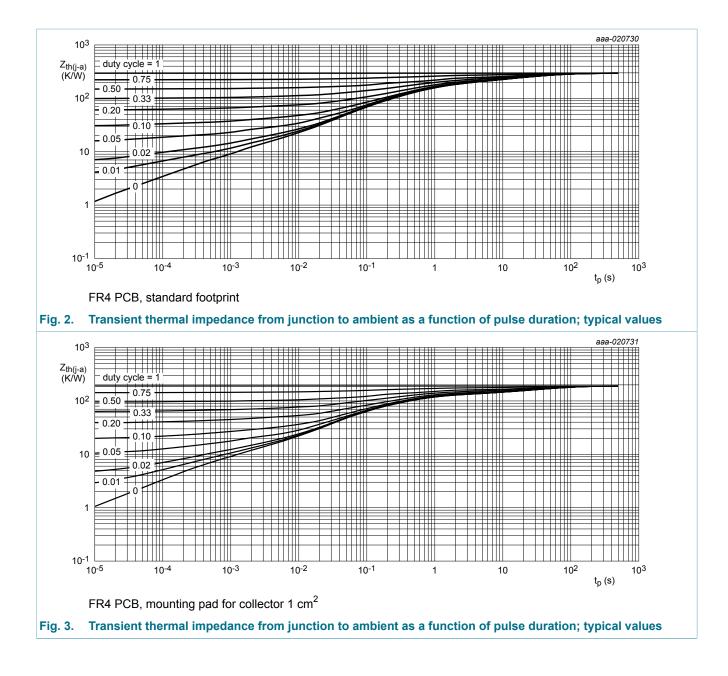
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

- ^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- ^[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

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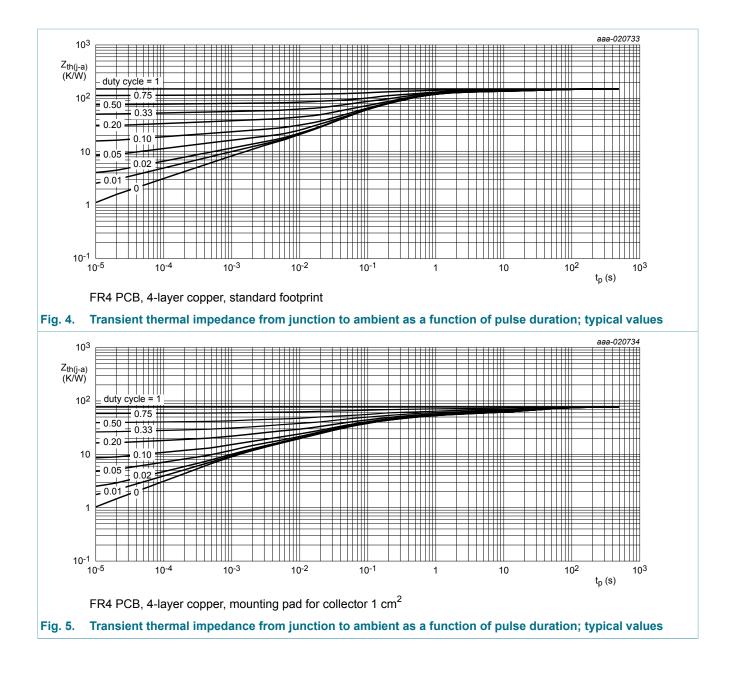
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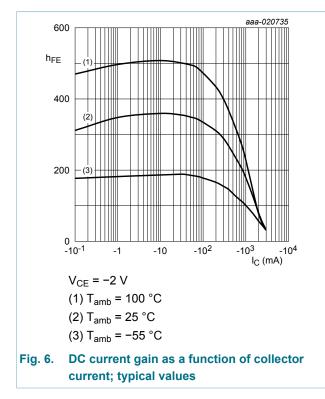
10. Characteristics

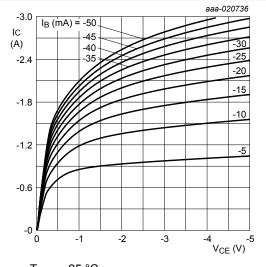
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off	V_{CB} = -44 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -44 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -44 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
ЕВО	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$\label{eq:Vce} \begin{split} V_{CE} &= -2 \ V; \ I_C = -100 \ m\text{A}; \ \text{pulsed}; \\ t_p &\leq 300 \ \mu\text{s}; \ \bar{\delta} &\leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$	170	250	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= -2 \ V; \ I_C = -500 \ m\text{A}; \ \text{pulsed}; \\ t_p &\leq 300 \ \mu\text{s}; \ \bar{\delta} &\leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$	140	200	-	
		V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	110	150	-	
		$V_{CE} = -2 \text{ V; } I_C = -2 \text{ A; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	50	75	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-80	-120	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-170	-250	mV
		$\begin{split} I_{C} &= -0.7 \text{ A}; \ I_{B} &= -7 \text{ mA}; \ \text{pulsed}; \\ t_{p} &\leq 300 \ \mu\text{s}; \ \delta &\leq 0.02 \ \ ; \ T_{amb} = 25 \ ^{\circ}\text{C} \end{split}$	-	-300	-420	mV
		I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-300	-450	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	250	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -0.5 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.89	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1	V
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-1.13	-1.25	V
V _{BE}	base-emitter voltage	$\begin{split} I_{C} &= -0.5 \text{ A}; \text{ V}_{CE} = -2 \text{ V}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta_{factor} \leq 0.02; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-0.76	-0.9	V
t _d	delay time	I_{C} = -1 A; I_{Bon} = -50 mA; I_{Boff} = 50 mA;	-	10	-	ns
r	rise time	T _{amb} = 25 °C	-	80	-	ns
ton	turn-on time		-	90	-	ns

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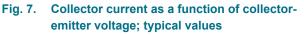
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _s	storage time		-	195	-	ns
t _f	fall time		-	75	-	ns
t _{off}	turn-off time		-	270	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -500 mA; f = 100 MHz; T _{amb} = 25 °C	-	100	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	16	-	pF

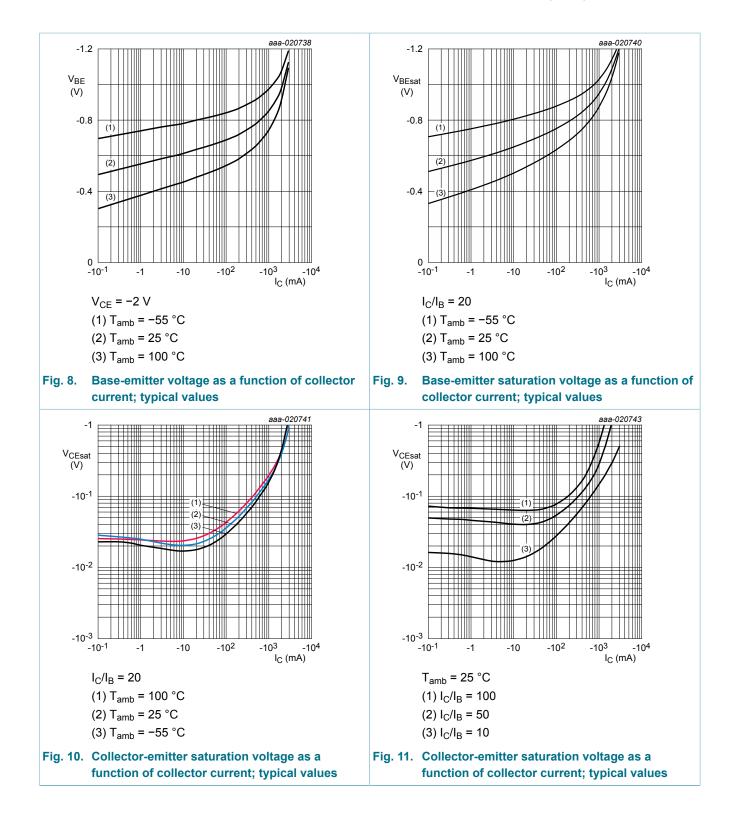








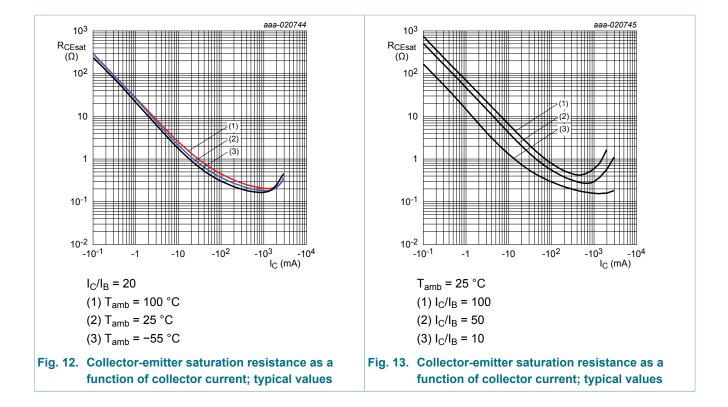
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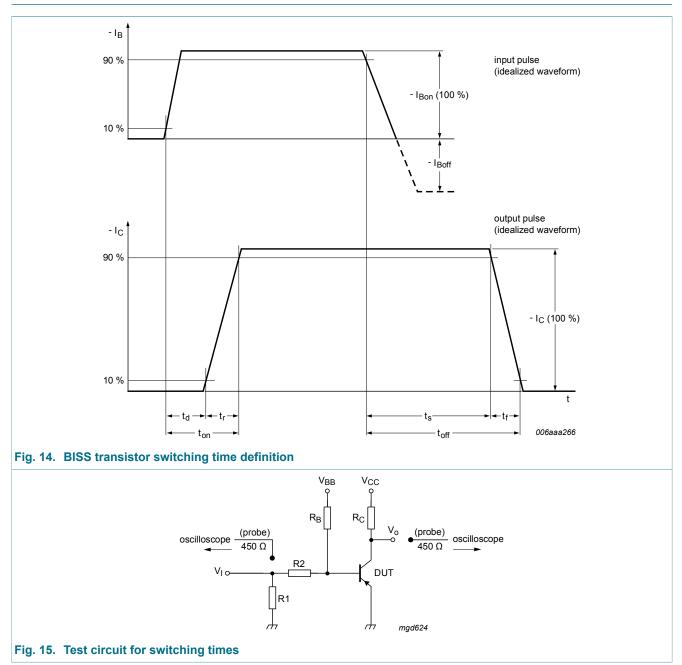
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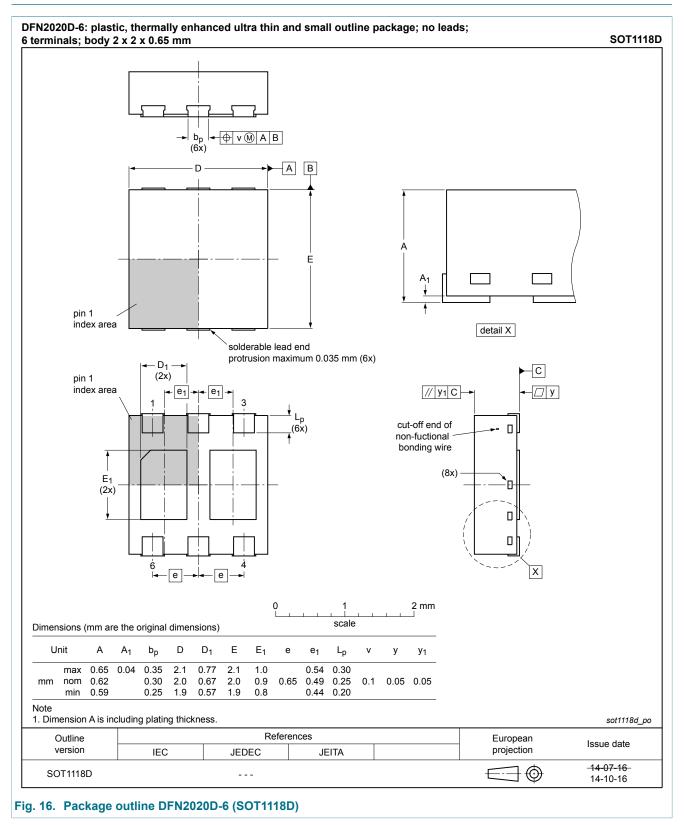
11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



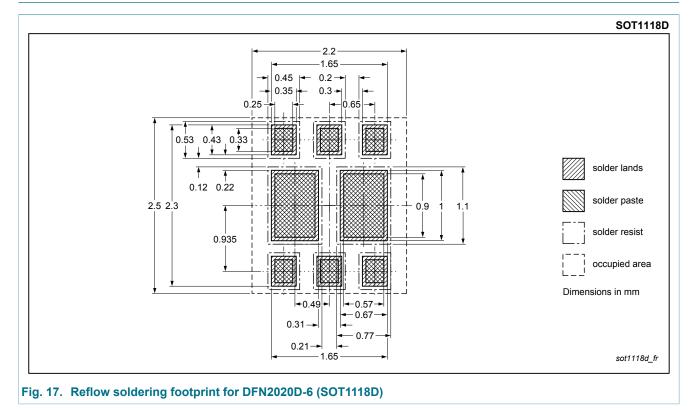
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13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS5255PAPS v.1	20151211	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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